

Amendments to the Claims

Claims 1-12. (Cancelled)

Claim 13. (Currently Amended) A semiconductor light emitting device comprising:

an electrode;

a substrate;

gallium nitride type compound semiconductor layers ~~having~~ forming a light emitting portion, said ~~compound~~ semiconductor layers including at least an n-type layer and a p-type layer, said ~~compound~~ semiconductor layers being ~~stacked on~~ between said electrode and said substrate;

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a ~~buffer layer being~~ region interposed between said substrate and said semiconductor layers;

wherein ~~at least said substrate side of said buffer layer contains at least one kind of element selected from a group consisting of~~ region comprises a first layer, said first layer including In, P and As.

Claim 14. (Currently Amended) The semiconductor light emitting device according to Claim claim13, wherein said buffer layer region has includes a low second layer formed at a first temperature buffer layer consists of $\text{In}_d\text{Ga}_{1-d}\text{N}$ ($0 < d < 1$) or $\text{In}_d\text{Al}_e\text{Ga}_{1-d-e}\text{N}$ ($0 < d < 1$, $0 < e < 1$, $0 < d+e < 1$) on said substrate, and wherein said first layer includes the elements In, Ga, and N, said first layer being formed at a second temperature higher than said first temperature.

Claim 15. (Cancelled)

Claim 16. (Currently Amended) The semiconductor light emitting device according to ~~Claim 13~~claim 14, wherein at least said substrate side the conductivity of said the buffer first layer is a semiconductor greater than the conductivity of the second layer where a minimum electric current flows.

Claim 17. (Cancelled)

Claim 18. (Currently Amended) The semiconductor light emitting device according to ~~Claim~~claim 16, wherein at least said substrate side of said buffer the second layer consists of a semiconductor layer of high resistance.

Claim 19. (Cancelled)

Claim 20. (Currently Amended) The semiconductor light emitting device according to ~~Claim~~claim 13, wherein said buffer layer consists of region further comprises a p-type low temperature buffer second layer formed at low a first temperature on the surface of said substrate and high, wherein said first layer is formed at a second temperature higher than said first temperature buffer, said first layer formed at high temperature on said low temperature buffer being between said second layer with at least the surface side made into an n-type; wherein on said high temperature buffer layer are formed sequentially an n-type clad layer, active layer, a p-type clad layer,

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and p-type and said semiconductor layers, said light emitting device further including
a p-type contact layer in that order, wherein a p-side between said semiconductor
layers and said electrode is formed on said n-type clad layer or on a high temperature
buffer layer exposed by etching.

Claim 21. (Currently Amended) The semiconductor light emitting device according
to Claim claim 20, wherein said low and high temperature buffer layers p-type contact
layer consists of essentially GaN; wherein said n-type and p-type clad layers
respectively consist of $Al_kGa_{1-k}N$ ($0 < k < 1$); wherein said active layer consists of
 $Ga_yIn_{1-y}N$ ($0 < y < 1$), and wherein said p-type contact layer consists of GaN.

Claims 22-52. (Cancelled)

Claims 53. (New) The semiconductor light emitting device according to claim 13,
wherein said buffer region further comprises a second layer formed at a first
temperature on the surface of said substrate, wherein said first layer includes the
elements In, Ga, and N, and said first layer is formed at a second temperature higher
than said first temperature, said first layer being between said second layer and said
semiconductor layers, said light emitting device further including a p-type contact
layer between said semiconductor layers and said electrode.

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